

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

MCH3477 — General-Purpose Switching Device Applications

Features

- · Ultrahigh speed switching
- · Halogen free compliance

- 1.8V drive
- · Protection diode in

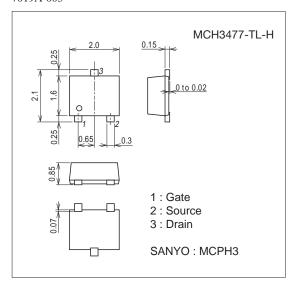
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	ID		4.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	18	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

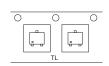
unit : mm (typ) 7019A-003



Product & Package Information

Package : MCPH3
 JEITA, JEDEC : SC-70, SOT-323
 Minimum Packing Quantity : 3,000 pcs./reel

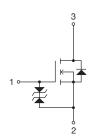
Packing Type: TL



Marking



Electrical Connection

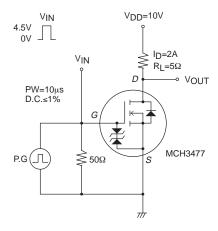


http://semicon.sanyo.com/en/network

Electrical Characteristics at Ta=25°C

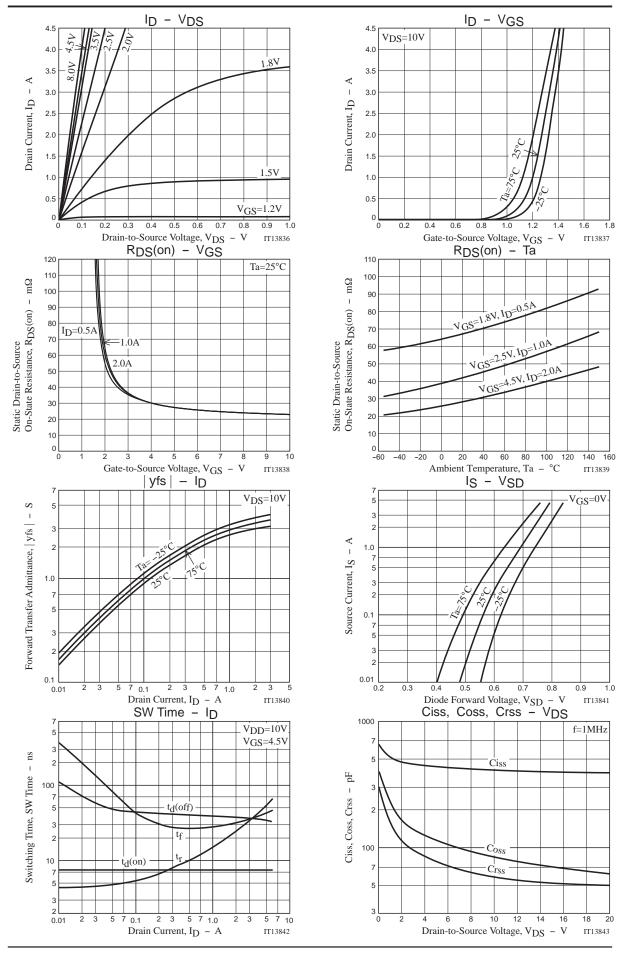
Parameter	Coursells and	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Uilit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =2A	2.0	3.4		S	
	RDS(on)1	ID=2A, VGS=4.5V		29	38	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =1A, V _{GS} =2.5V		43	61	mΩ	
	RDS(on)3	ID=0.5A, VGS=1.8V		69	99	$m\Omega$	
Input Capacitance	Ciss			410		pF	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		84		pF	
Reverse Transfer Capacitance	Crss			59		pF	
Turn-ON Delay Time	t _d (on)			7.5		ns	
Rise Time	t _r	Con an arified Took Civarit		26		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		38		ns	
Fall Time	tf			32		ns	
Total Gate Charge	Qg			5.1		nC	
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =4.5A		0.7		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		1.7		nC	
Diode Forward Voltage	V _{SD}	I _S =4.5A, V _{GS} =0V		0.78	1.2	V	

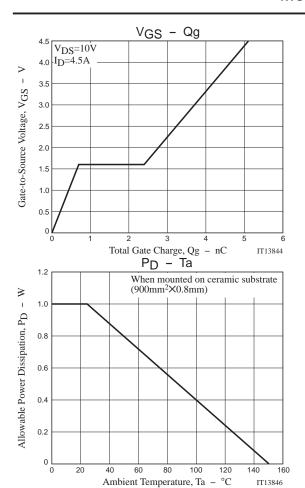
Switching Time Test Circuit

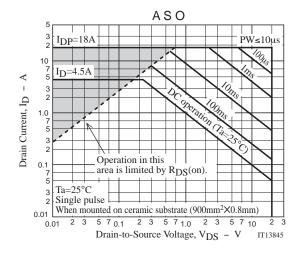


Ordering Information

Device	Package	Shipping	memo	
MCH3477-TL-H	МСРН3	3,000pcs./reel	Pb Free and Halogen Free	





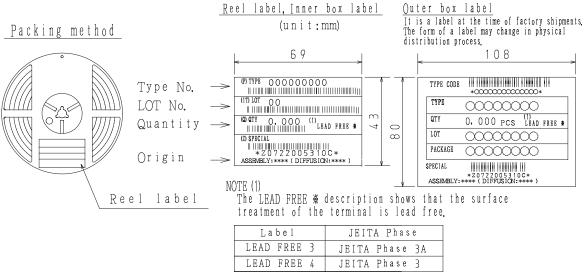


Taping Specification

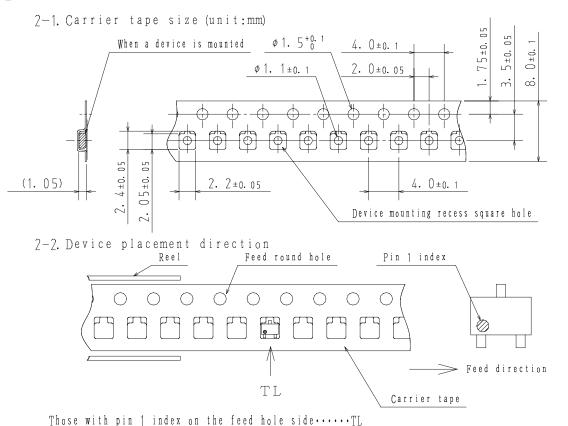
MCH3477-TL-H

1. Packing Format

Package Name	Carrier Tape	Maximun Number of devices contained (pcs)			Packing	g format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)		
мсрн3	мсрн3	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained		
					Dimensions:mm (external)	Dimensions:mm (external)		
					183×72×185	440×195×210		

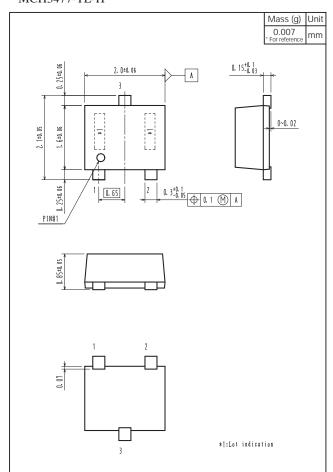


2. Taping configuration

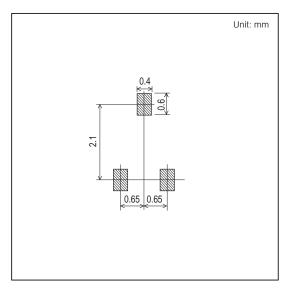


Outline Drawing

MCH3477-TL-H



Land Pattern Example



Note on usage: Since the MCH3477 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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